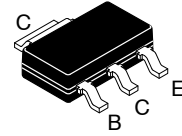


NPN Darlington Transistor

NZT7053

This device is designed for applications requiring extremely high gain at collector currents to 1.0 A and high breakdown voltage. Sourced from Process 06.



SOT-223
CASE 318H

ABSOLUTE MAXIMUM RATINGS (Notes 1, 2)

($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Symbol	Parameter	Value	Unit
V_{CEO}	Collector-Emitter Voltage	100	V
V_{CB0}	Collector-Base Voltage	100	V
V_{EB0}	Emitter-Base Voltage	12	V
I_C	Collector Current - Continuous	1.5	A
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- These ratings are based on a maximum junction temperature of 150°C .
- These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

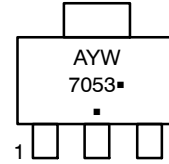
THERMAL CHARACTERISTICS (Note 3)

($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Symbol	Characteristics	Value	Unit
P_D	Total Device Dissipation	1000	mW
	Derate Above 25°C	8.0	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	$^\circ\text{C}/\text{W}$

- Device mounted on FR-4 PCB $36\text{ mm} \times 18\text{ mm} \times 1.5\text{ mm}$; mounting pad for the collector lead min. 6 cm^2 .

MARKING DIAGRAM



A = Assembly Location
Y = Year
W = Work Week
7053 = Specific Device Code
■ = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
NZT7053	SOT-223 (Pb-Free)	4000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](#).

NZT7053

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Symbol	Parameter	Conditions	Min.	Max.	Unit
--------	-----------	------------	------	------	------

OFF CHARACTERISTICS

V _{(BR)CEO}	Collector–Emitter Breakdown Voltage (Note 4)	I _C = 1.0 mA, I _B = 0	100	–	V
V _{(BR)CBO}	Collector–Base Breakdown Voltage	I _C = 100 μA, I _E = 0	100	–	V
V _{(BR)EBO}	Emitter–Base Breakdown Voltage	I _E = 1.0 mA, I _C = 0	12	–	V
I _{CBO}	Collector–Cutoff Current	V _{CB} = 80 V, I _E = 0	–	0.1	μA
I _{CES}	Emitter–Cutoff Current	V _{CE} = 80 V, I _E = 0	–	0.2	μA
I _{EBO}	Emitter–Cutoff Current	V _{EB} = 7.0 V, I _C = 0	–	0.1	μA

ON CHARACTERISTICS (Note 4)

h _{FE}	DC Current Gain	I _C = 100 mA, V _{CE} = 5.0 V	10000	–	
		I _C = 1.0 A, V _{CE} = 5.0 V	1000	20000	
V _{CE(sat)}	Collector–Emitter Saturation Voltage	I _C = 100 mA, I _B = 0.1 mA	–	1.5	V
V _{BE(on)}	Base–Emitter On Voltage	I _C = 100 mA, V _{BE} = 5.0 V	–	2.0	V

SMALL SIGNAL CHARACTERISTICS

F _T	Transition Frequency	I _C = 100 mA, V _{CE} = 5.0 V	200	–	MHz
----------------	----------------------	--	-----	---	-----

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse test: pulse width ≤ 300 μs, duty cycle ≤ 2%

TYPICAL CHARACTERISTICS

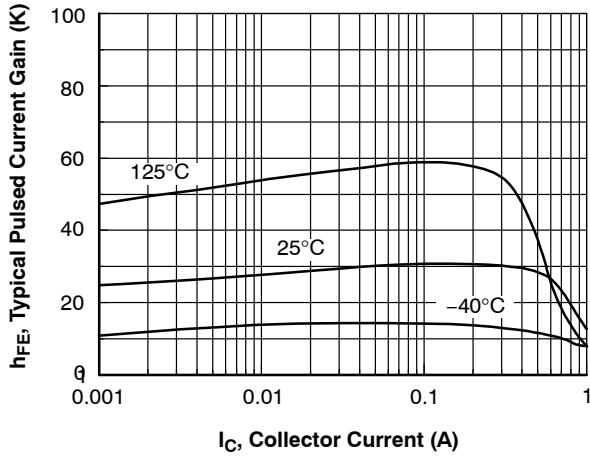


Figure 1. Typical Pulsed Current Gain vs. Collector Current

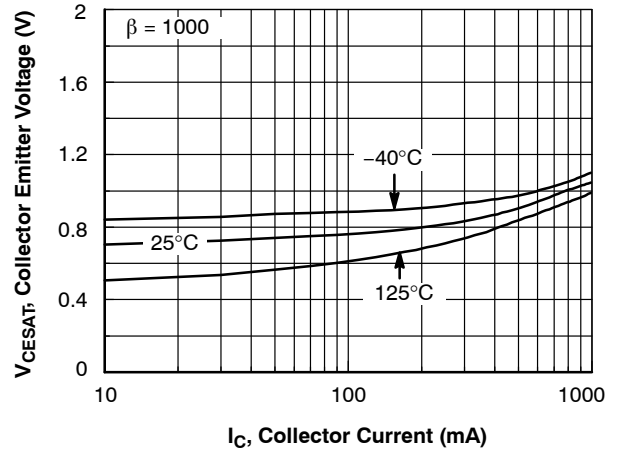


Figure 2. Collector-Emitter Saturation Voltage vs. Collector Current

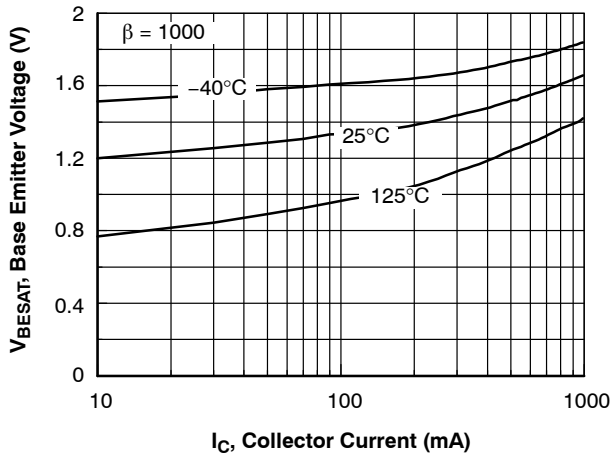


Figure 3. Base-Emitter Saturation Voltage vs. Collector Current

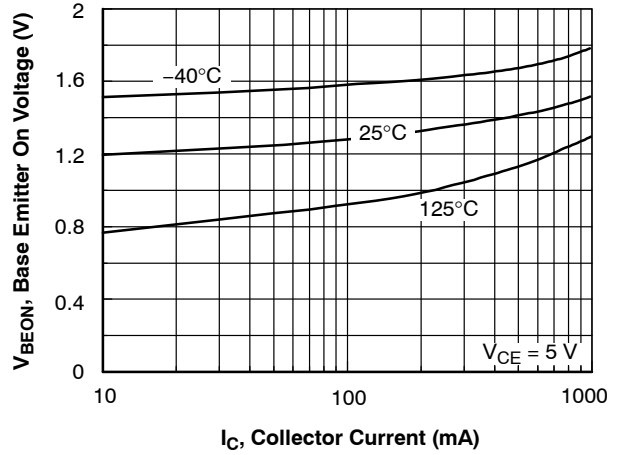


Figure 4. Base Emitter ON Voltage vs. Collector Current

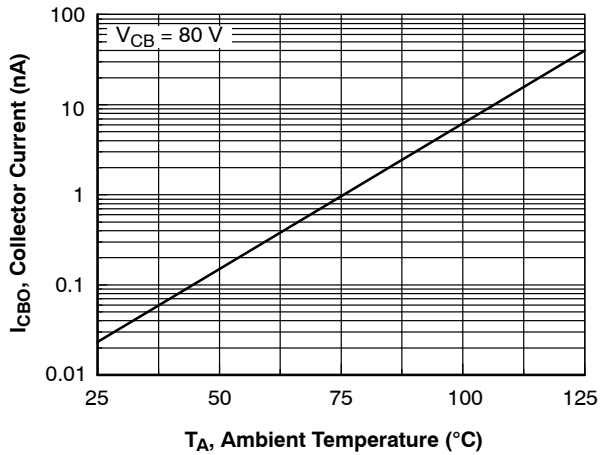


Figure 5. Collector-Cutoff Current vs. Ambient Temperature

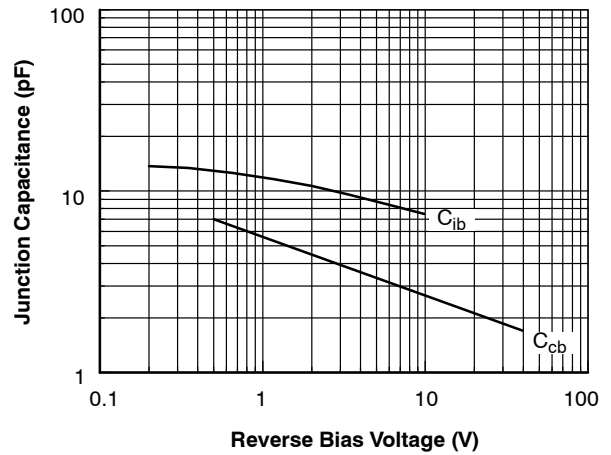


Figure 6. Junction Capacitance vs. Reverse Bias Voltage

TYPICAL CHARACTERISTICS (continued)

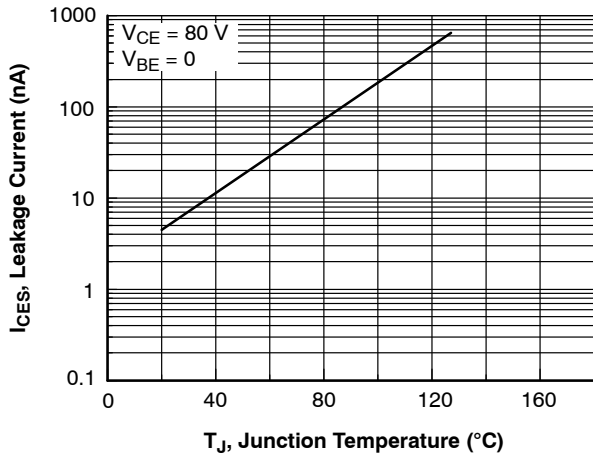


Figure 7. Typical Collector-Emitter Leakage Current vs. Temperature

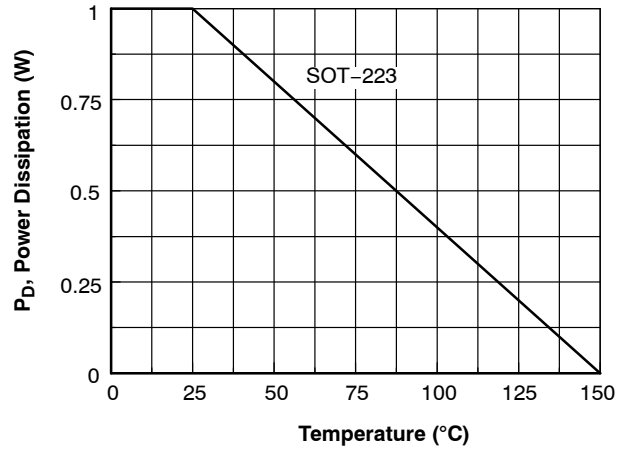


Figure 8. Power Dissipation vs. Ambient Temperature

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SOT-223
CASE 318H
ISSUE B

DATE 13 MAY 2020

SCALE 2:1



TOP VIEW

$\Phi 0.10 \text{ (M)}$ C A B

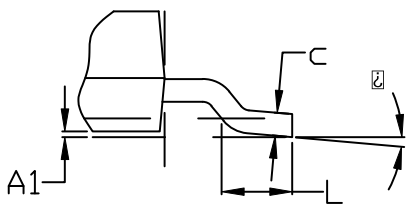
NOTE 7



SIDE VIEW



END VIEW



DETAIL A

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D & E1 ARE DETERMINED AT DATUM H. DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. SHALL NOT EXCEED 0.23mm PER SIDE.
4. LEAD DIMENSIONS b AND b1 DO NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION IS 0.08mm PER SIDE.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
7. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

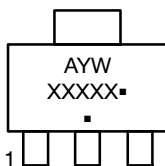
DIM	MILLIMETERS		
	MIN.	NDM.	MAX.
A	---	---	1.80
A1	0.02	0.06	0.11
b	0.60	0.74	0.88
b1	2.90	3.00	3.10
c	0.24	---	0.35
D	6.30	6.50	6.70
E	6.70	7.00	7.30
E1	3.30	3.50	3.70
e	2.30 BSC		
L	0.25	---	---
\square	0°	---	10°



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

GENERIC MARKING DIAGRAM*



- A = Assembly Location
- Y = Year
- W = Work Week
- XXXXX = Specific Device Code
- = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98ASH70634A	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOT-223	PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales